## <u>Silicon Carbide Schottky</u> <u>Diode</u>

### 650 V, 6 A

## FFSB0665B

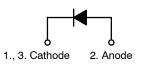
Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.



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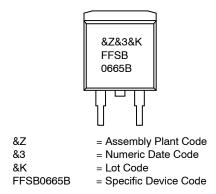
V <sub>RRM</sub>	I <sub>F</sub>
650 V	6.0 A



Schottky Diode



#### MARKING DIAGRAM



#### **ORDERING INFORMATION**

See detailed ordering and shipping information on page 2 of this data sheet.

#### Features

- Max Junction Temperature 175°C
- Avalanche Rated 24.5 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery / No Forward Recovery
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

#### Applications

- General Purpose
- SMPS, Solar Inverter, UPS
- Power Switching Circuits

#### MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise noted)

Parameter	Symbol	Value	Unit		
Peak Repetitive Reverse Voltage	V <sub>RRM</sub>	650	V		
Single Pulse Avalanche Energy ( $I_{L(pk)} = 9.9 \text{ A}, L = 0.5 \text{ mH}, V = 50 \text{ C}$	E <sub>AS</sub>	24.5	mJ		
Continuous Rectified Forward	@ T <sub>C</sub> < 150	١ <sub>F</sub>	6.0	А	
Current	@ T <sub>C</sub> < 135		8.0		
Non-Repetitive Peak Forward Surge Current	T <sub>C</sub> = 25°C t <sub>P</sub> = 10 μs	I <sub>FM</sub>	523	A	
	T <sub>C</sub> = 150°C t <sub>P</sub> = 10 μs		467		
Non-Repetitive Forward Surge Current (Half-Sine Pulse)	T <sub>C</sub> = 25°C t <sub>P</sub> = 8.3 ms	I <sub>FSM</sub>	45	A	
Power Dissipation	T <sub>C</sub> = 25°C	P <sub>tot</sub>	61	W	
	T <sub>C</sub> = 150°C		10		
Operating Junction and Storage T Range	T <sub>J</sub> , T <sub>stg</sub>	–55 to +175	°C		

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

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#### THERMAL CHARACTERISTICS

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case, Max.		2.46	°C/W

#### **ELECTRICAL CHARACTERISTICS** (T<sub>J</sub> = $25^{\circ}$ C unless otherwise noted)

Parameter Symbol		Test Conditions		Тур	Max	Unit	
ON CHARACTERISTICS	·			•			
Forward Voltage	V <sub>F</sub>	$I_F = 6.0 \text{ A}, \text{ T}_J = 25^{\circ}\text{C}$		1.38	1.7	V	
		$I_F = 6.0 \text{ A},  T_J = 125^{\circ}\text{C}$		1.53	2.0		
		$I_F = 6.0 \text{ A},  T_J = 175^{\circ}\text{C}$		1.67	2.4		
Reverse Current	I <sub>R</sub>	$V_{R} = 650 \text{ V}, \text{ T}_{J} = 25^{\circ}\text{C}$		0.5	40	μA	
		$V_{R} = 650 \text{ V}, \text{ T}_{J} = 125^{\circ}\text{C}$		1.0	80		
		$V_{R} = 650 \text{ V}, \text{ T}_{J} = 175^{\circ}\text{C}$		2.0	160		

#### CHARGES, CAPACITANCES & GATE RESISTANCE

Total Capacitive Charge	Q <sub>C</sub>	V <sub>C</sub> = 400 V	16	nC
	C <sub>tot</sub>	V <sub>R</sub> = 1 V, f = 100 kHz	259	pF
		V <sub>R</sub> = 200 V, f = 100 kHz	29	
		V <sub>R</sub> = 400 V, f = 100 kHz	22	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

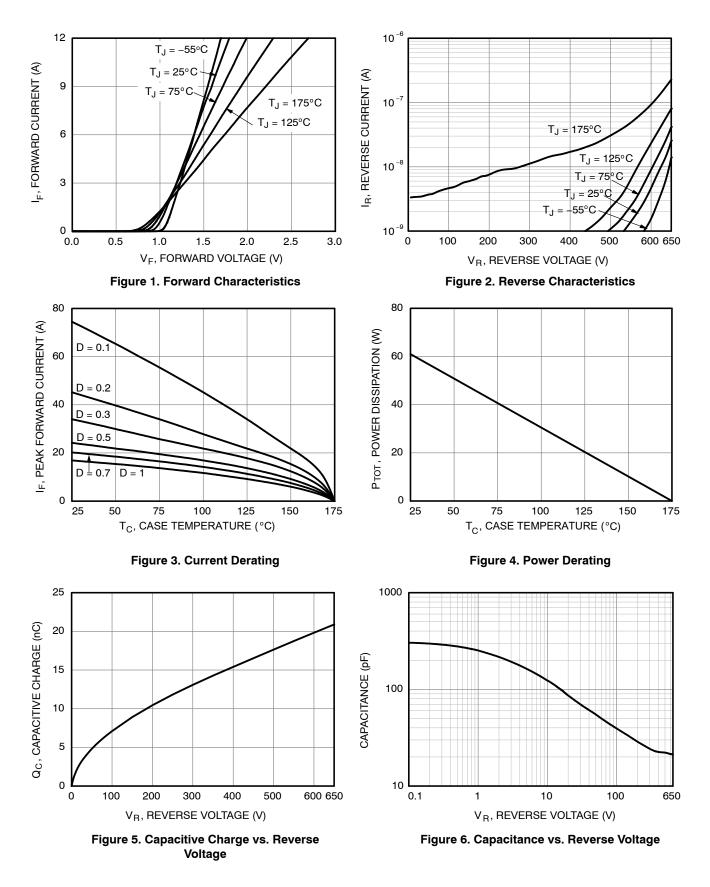
#### PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Marking	Package	Packing Method	Reel Size	Tape Width	Quantity
FFSB0665B	FFSB0665B	D <sup>2</sup> PAK	Tape & Reel <sup>†</sup>	330 mm	24 mm	800 Units

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, <u>BRD8011/D</u>.

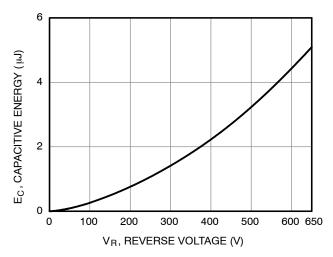
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#### **TYPICAL CHARACTERISTICS**



#### FFSB0665B

#### **TYPICAL CHARACTERISTICS**





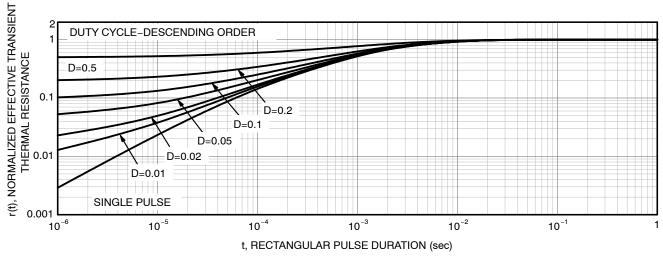
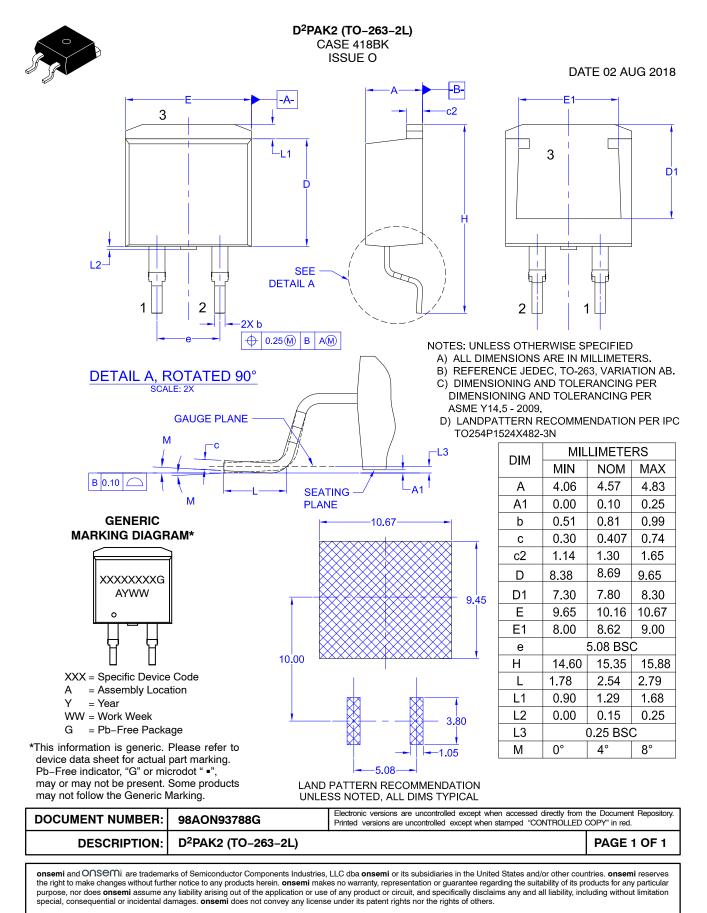


Figure 8. Junction-to-Case Transient Thermal Response

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